

**AMENDMENTS TO THE CLAIMS**

The status of the claims of the present application stands as follows:

**Claim 1 (cancelled)**

2. **(currently amended)** An exhaust gas scrubber system according to claim 1 26, wherein said at least one substrate is made of quartz.
3. **(currently amended)** An exhaust gas scrubber system according to claim 1 26, wherein said at least one substrate forms a baffle.
4. **(currently amended)** An exhaust gas scrubber system according to claim 3, wherein said baffle includes a plurality of apertures for allowing the exhaust gas ~~stream~~ to flow through said baffle.
5. **(currently amended)** An exhaust gas scrubber system according to claim 1 26, further comprising a plurality of said substrates forming a series of baffles within said chamber.
6. **(currently amended)** An exhaust gas scrubber system according to claim 5, wherein each baffle of said series of baffles includes a plurality of apertures for allowing the exhaust gas ~~stream~~ to flow through each of said series of baffles.
7. **(currently amended)** An exhaust gas scrubber system according to claim 5, wherein said series of baffles define a serpentine passageway within said CVD chamber.
8. **(currently amended)** An exhaust gas scrubber system according to claim 1 26, further comprising a heating element for heating at least one of said ~~enclosure~~ second chamber and said at least one substrate.

9. (currently amended) An exhaust gas scrubber system according to claim 1 26, wherein said at least one substrate is removable and reusable after the film has been removed.
10. (currently amended) An exhaust gas scrubber system according to claim 1 26, wherein the at least one chemical component of the exhaust gas is silicon.

Claims 11-14 (withdrawn)

15. (currently amended) A scrubber system for scrubbing a gas containing a non-toxic part and a toxic part, the scrubber comprising:
- a. a processing chamber;
  - b. a first ~~enclosure~~ apparatus ~~defining a first chamber for receiving the gas, said first chamber in fluid communication with said processing chamber and adapted for removing at least a portion of the non-toxic part of the exhaust gas by chemical vapor deposition;~~ and
  - c. a second ~~enclosure~~ apparatus ~~defining a second chamber in fluid communication with said first chamber, said second chamber for receiving at least a portion of the gas, said second chamber in fluid communication with said processing chamber and adapted for removing at least a portion of the toxic part from the gas.~~
16. (currently amended) A scrubber system according to claim 15, further comprising a substrate located in said first ~~enclosure~~ apparatus, said substrate for receiving by chemical vapor deposition a film containing the non-toxic part of the gas.
17. (currently amended) A scrubber system according to claim 15, wherein the non-toxic part comprises silicon.
18. (currently amended) A scrubber system according to claim 15, wherein the toxic part comprises arsenic.

Claims 19-25 (withdrawn)

26. (new) An exhaust gas scrubber system for removing at least one chemical component of an exhaust gas by chemical vapor deposition of a film, the scrubber comprising:
- a. a first chamber adapted for processing a structure in a manner that the exhaust gas is produced;
  - b. a second chamber in fluid communication with said first chamber and adapted for chemical vapor deposition of the at least one chemical component of the exhaust gas; and
  - c. at least one substrate contained within said second chamber and having a film deposition surface for receiving the film.

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